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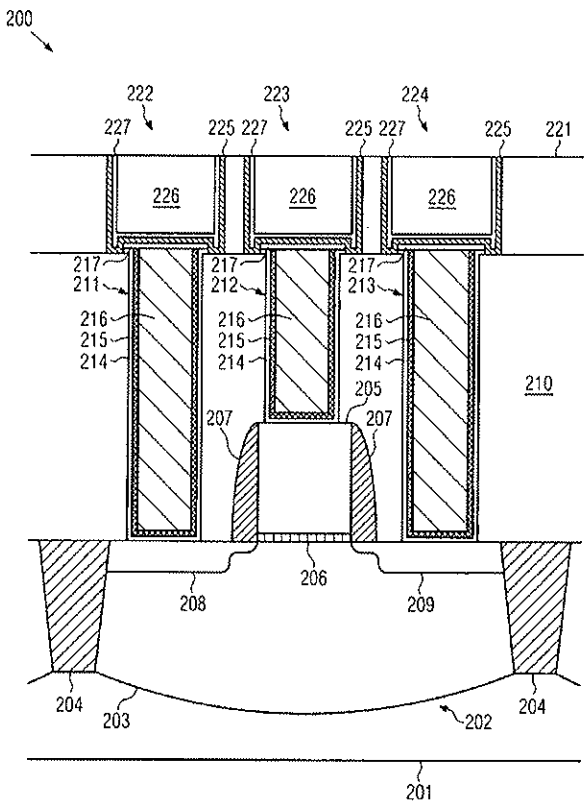
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(54) Title: SEMICONDUCTOR STRUCTURE WITH INTERCONNECT COMPRISING SILVER AND METHOD OF FORMING THE SAME



(57) Abstract: A method of forming a semiconductor structure comprises providing a semiconductor substrate comprising a layer of a dielectric material (210). A recess is provided in the layer of dielectric material. The recess is filled with a material comprising silver (216), possibly encapsulated by rhodium (214), (217).

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